

BCX71H PNP EPITAXIAL SILICON TRANSISTOR

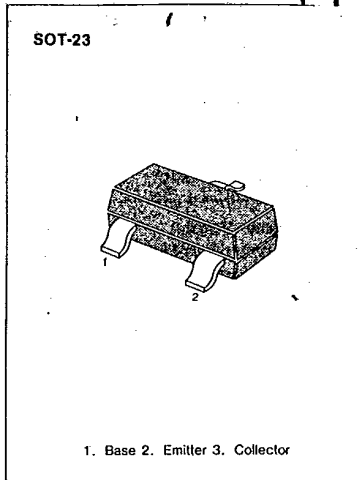
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GENERAL PURPOSE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	45	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5086 for graphs



ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =2mA, I _B =0	45		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =1μA, I _C =0	5		V
Collector Cutoff Current	I _{CES}	V _{CE} =32V, V _{BE} =0		20	nA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =10μA	30		
		V _{CE} =5V, I _C =2mA	140	310	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	V _{CE} =1V, I _C =50mA	80		
		I _C =10mA, I _B =0.25mA		0.25	V
		I _C =50mA, I _B =1.25mA		0.55	V
Base-Emitter Saturation Voltage	V _{BE} (sat)	I _C =10mA, I _B =0.25mA	0.6	0.85	V
		I _C =50mA, I _B =1.25mA	0.68	1.05	V
Base-Emitter On Voltage	V _{BE} (on)	I _C =2mA, V _{CE} =5V	0.6	0.75	V
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0		6	pF
		f=1MHz			
Noise Figure	NF	I _C =0.2mA, V _{CE} =5V f=1KHz, R _S =2KΩ		6	dB
Turn On Time	t _{on}	I _C =10mA, I _{B1} =1mA		150	ns
Turn Off Time	t _{off}	I _{B2} =1mA, V _{EB} =3.6V R _L =990Ω		800	ns

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Marking

